

**DL-3149-054****Index Guided AlGaInP Laser Diode****Overview**

DL-3149-054 is 670 nm (Typ.) index guided AlGaInP laser diode with low threshold current and high operating temperature. The low threshold current and high operating temperature are achieved by the use of a strained multiple quantum well active layer. DL-3149-054 is suitable for applications such as bar-code scanners, laser pointers and other optical information systems.

Features

- Short wavelength : 670 nm (Typ.)
- High operating temperature : 60°C at 5 mW
- Low threshold current : $I_{th} = 30$ mA (Typ.)
- Small package : 5.6 mm ϕ

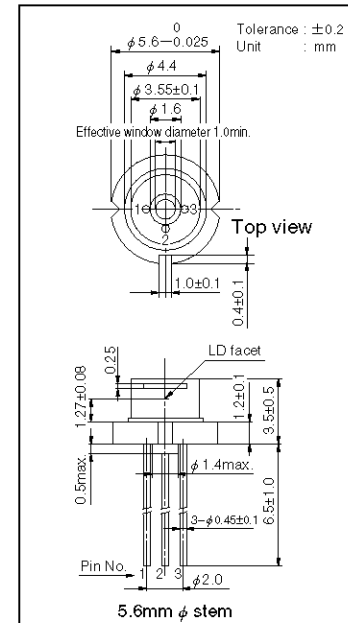
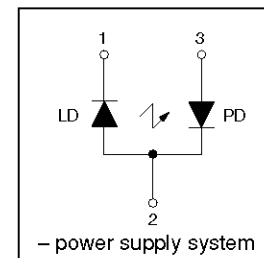
Absolute Maximum Ratings at $T_c=25^\circ\text{C}$

Parameter	Symbol	Ratings	Unit
Light Output	P_o	5	mW
Reverse Voltage	Laser	2	V
	PIN	30	
Operating Temperature	T_{opr}	-10 to +60	°C
Storage Temperature	T_{stg}	-40 to +85	°C

Electrical and Optical Characteristics at $T_c=25^\circ\text{C}$

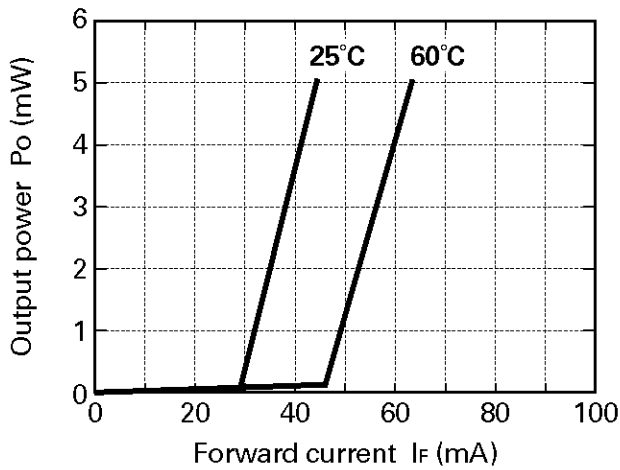
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Threshold Current	I_{th}	CW	-	30	50	mA
Operating Current	I_{op}	$P_o=5\text{mW}$	-	45	60	mA
Operating Voltage	V_{op}	$P_o=5\text{mW}$	-	2.3	2.6	V
Lasing Wavelength	λ_p	$P_o=5\text{mW}$	660	670	680	nm
Beam Divergence ※)	Perpendicular	θ_{\perp}	25	33	40	deg.
	Parallel	θ_{\parallel}	6	8	10	deg.
Off Axis Angle	Perpendicular	$\Delta\theta_{\perp}$	-	-	± 3	deg.
	Parallel	$\Delta\theta_{\parallel}$	-	-	± 3	deg.
Differential Efficiency	dP_o/dI_{op}	-	0.15	0.3	-	mW/mA
Monitoring Output Current	I_m	$P_o=5\text{mW}$	0.4	1.2	2.0	mA
Astigmatism	A_s	$P_o=5\text{mW}$	-	8	-	μm

※) Full angle at half maximum note : The above product specifications are subject to change without notice.

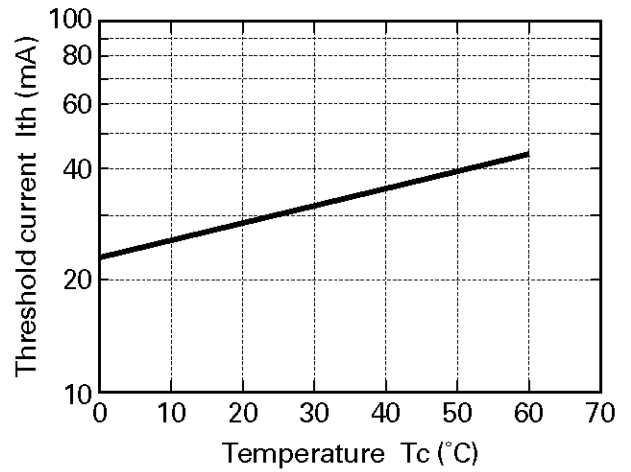
Package Dimensions**Electrical Connection**

Characteristics

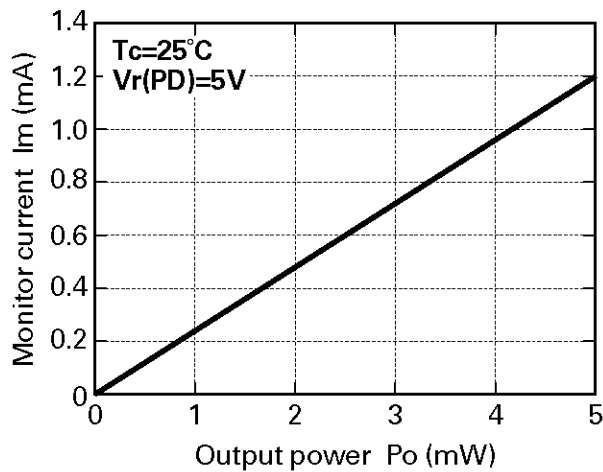
Output power vs. Forward current



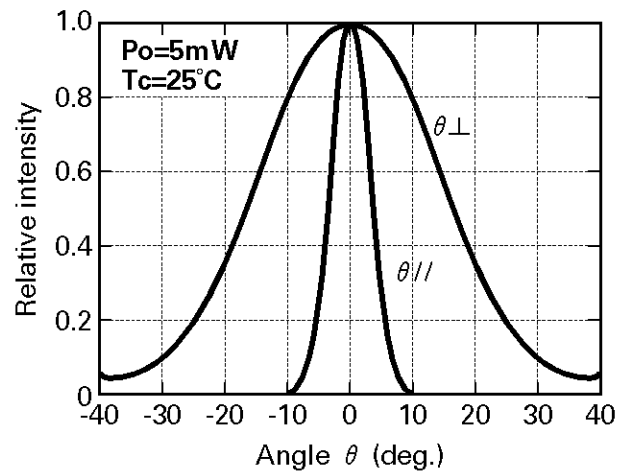
Threshold current vs. Temperature



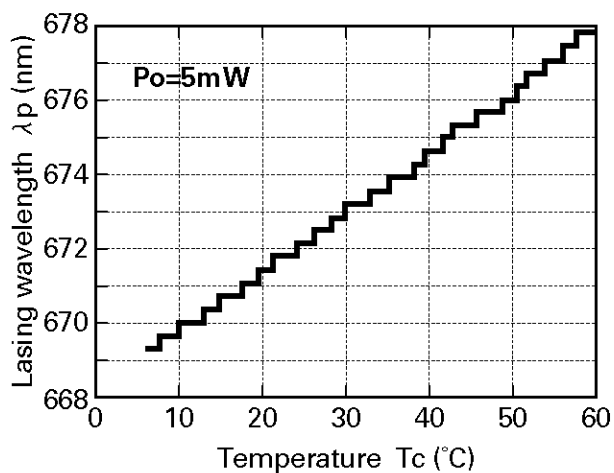
Monitor current vs. Output power



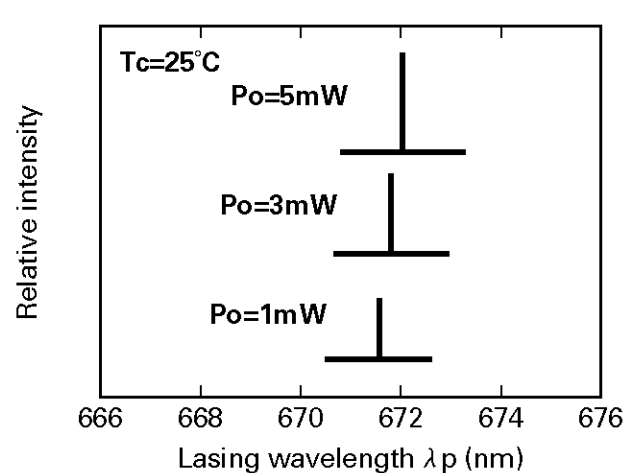
Beam divergence



Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength



 **CAUTION**

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Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

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